

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page [0094] with the following amended paragraph:

[0094] Subsequently, as shown in Fig. 3B, a surface portion of the silicon oxide film 310 is removed by etching so that the portion of a high implantation concentration of silver becomes located near a top surface. That is, the silicon oxide film 240 310 is etched to a depth equivalent to or deeper than the above-mentioned implantation depth. In the present embodiment, the etching was effected to a depth of about 50 nm from the surface. The etching method may be either one of wet etching or dry etching similarly to the second embodiment. In the present embodiment, the wet etching was carried out by using a hydrofluoric acid solution of a concentration of 0.5%.